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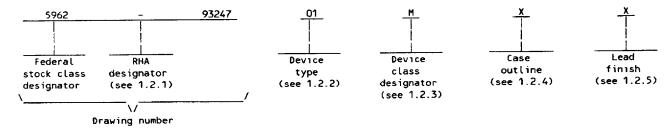
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1. SCOPE

- 1.1 <u>Scope</u>. This drawing forms a part of a one part one part number documentation system (see 6.6 herein). Two product assurance classes consisting of military high reliability (device classes Q and M) and space application (device class V), and a choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). Device class M microcircuits represent non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices". When available, a choice of radiation hardness assurance (RHA) levels are reflected in the PIN.
- 1.2 PIN. The PIN shall be as shown in the following example:



- 1.2.1 RHA designator. Device class M RHA marked devices shall meet the MIL-I-38535 appendix A specified RHA levels and shall be marked with the appropriate RHA designator. Device classes Q and V RHA marked devices shall meet the MIL-I-38535 specified RHA levels and shall be marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
- 1.2.2 Device type(s). The device type(s) shall identify the circuit function as follows:

Device type	Generic number	<u>Circuit function</u>	Access time
01	7256E	256 macrocell EEPLD	20 ns
02	7256E	256 macrocell EEPLD	15 ns

1.2.3 <u>Device class designator</u>. The device class designator shall be a single letter identifying the product assurance level (see 6.6 herein) as follows:

Device class

Device requirements documentation

м

Vendor self-certification to the requirements for non-JAN class B microcircuits in accordance with 1.2.1 of MIL-STD-883

Q or V

Certification and qualification to MIL-I-38535

1.2.4 <u>Case outline(s)</u>. The case outline(s) shall be as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package_style		
X	CMGA7-P192	192 <u>1</u> /	pin grid array		
Y	see figure 1	208 2 /	quad-flat package		

1.2.5 <u>Lead finish</u>. The lead finish shall be as specified in MIL-STD-883 (see 3.1 herein) for class M or MIL-I-38535 for classes Q and V. Finish letter "X" shall not be marked on the microcircuit or its packaging. The "X" designation is for use in specifications when lead finishes A, B, and C are considered acceptable and interchangeable without preference.

- 192 = actual number of pins used, not maximum listed in MIL-STD-1835.
- 2/ 208 = actual number of pins used, not maximum listed in MIL-STD-1835.

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supply voltage range with respect to ground (V_{CC}). Programming supply voltage range with respect to ground DC input voltage range with respect to ground (V_{IN}) DC V_{CC} or GND current (I_{MAX})	nd (V _{PP})	-2.0 V dc to +7.0 V d -2.0 V dc to +13.0 V d -2.0 V dc to +7.0 V d 800 mA ±25 mA -65°C to +150°C See MIL-STD-1835 12°C/W 5/ 4.0 W -65°C to +135°C +175°C 100 erase/write cycl 10 years (manimum)	dc <u>4</u> / c <u>4</u> /
.4 Recommended operating conditions.			
Supply voltage range (V_{CC})		+4.5 V dc to +5.5 V d O V dc to V _{CC} O V dc to V _{CC} 40 ns maximum 40 ns maximum -55°C to +125°C	dc
.5 Digital logic testing for device classes Q and V.			
Fault coverage measurement of manufacturing logic tests (MIL-STD-883, test method 5012)	. XX percent <u>6</u> /		
. APPLICABLE DOCUMENTS			
2.1 <u>Government specification, standards, bulletin, an</u> specification, standards, bulletin, and handbook of the iss Specifications and Standards specified in the solicitation,	us listed in that	nless otherwise specifie issue of the Department o this drawing to the extent	of Defense Index o
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HANDBOOK

MILITARY

MIL-HDBK-780- Standardized Military Drawings.

(Copies of the specification, standards, bulletin, and handbook required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 <u>Non-Government publications</u>. The following document(s) form a part of this document to the extent specified herein. Unless otherwise specified, the issues of the documents which are DoD adopted are those listed in the issue of the DoDISS cited in the solicitation. Unless otherwise specified, the issues of documents not listed in the DoDISS are the issues of the documents cited in the solicitation.

AMERICAN SOCIETY FOR TESTING AND MATERIALS (ASTM)

ASTM Standard F1192-88 - Standard Guide for the Measurement of Single Event Phenomena from Heavy Ion Irradiation of Semiconductor Devices.

(Applications for copies of ASTM publications should be addressed to the American Society for Testing and Materials, 1916 Race Street, Philadelphia, PA 19103.)

ELECTRONICS INDUSTRIES ASSOCIATION (EIA)

JEDEC Standard No. 17 - A Standardized Test Procedure for the Characterization of Latch-up in CMOS Integrated Circuits.

(Applications for copies should be addressed to the Electronics Industries Association, 2001 Pennsylvania Street, N.W., Washington, DC 20006.)

(Non-Government standards and other publications are normally available from the organizations that prepare or distribute the documents. These documents also may be available in or through libraries or other informational services.)

2.3 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device class M shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein. The individual item requirements for device classes Q and V shall be in accordance with MIL-I-38535, the device manufacturer's Quality Management (QM) plan, and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u> The design, construction, and physical dimensions shall be as specified in MIL-STD-883 (see 3.1 herein) for device class M and MIL-1-38535 for device classes Q and V and herein.
 - 3.2.1 <u>Case outline(s)</u>. The case outline(s) shall be in accordance with 1.2.4 herein and figure 1.
 - 3.2.2 Terminal connections. The terminal connections shall be as specified on figure 2.
 - 3.2.3 Truth table. The truth table shall be as specified in figure 3.
- 3.2.3.1 <u>Unprogrammed devices</u>. The truth table for unprogrammed devices for contracts involving no altered item drawing shall be as specified on figure 3. When required in screening (see 4.2 herein) or quality conformance inspection, groups A, C, D, or E (see 4.4 herein), the devices shall be programmed by the manufacturer prior to test. A minimum of 50 percent of the total number of logic cells shall be programmed for any altered item drawing pattern.
- 3.2.3.2 <u>Programmed devices</u>. The truth table for programmed devices shall be as specified by an attached altered item drawing.
 - 3.2.4 Radiation exposure circuit. The radiation exposure circuit will be provided when RHA product becomes available.

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- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.
- 3.5 <u>Marking</u>. The part shall be marked with the PIN listed in 1.2 herein. Marking for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein). In addition, the manufacturer's PIN may also be marked as listed in MIL-BUL-103. Marking for device classes Q and V shall be in accordance with MIL-I-38535.
- 3.5.1 <u>Certification/compliance mark</u>. The compliance mark for device class M shall be a "C" as required in MIL-STD-883 (see 3.1 herein). The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-I-38535.
- 3.6 <u>Certificate of compliance</u>. For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.7.2 herein). For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.7.1 herein). The certificate of compliance submitted to DESC-EC prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device class M the requirements of MIL-STD-883 (see 3.1 herein), or for device classes Q and V, the requirements of MIL-I-38535 and the requirements herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device class M in MIL-STD-883 (see 3.1 herein) or for device classes Q and V in MIL-I-38535 shall be provided with each lot of microcircuits delivered to this drawing
- 3.8 <u>Notification of change for device class M</u>. For device class M, notification to DESC-EC of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.
- 3.9 <u>Verification and review for device class M.</u> For device class M, DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 42 (see MIL-I-38535, appendix A).</u>
- 3.11 <u>Processing of EEPLDs</u> All testing requirements and quality assurance provisions herein shall be satisfied by the manufacturer prior to delivery.
- 3.12.1 <u>Conditions of the supplied devices</u>. Devices will be supplied in erased state. No provision will be made for supplying written devices.
- 3.12.2 Writing of EEPLDS. When specified, devices shall be written in accordance with the procedures and characteristics specified in 4.6.
- 3 12.3 <u>Clearing of EEPLDs</u>. When specified, devices shall be cleared in accordance with the procedures and characteristics specified in 4.7.
- 3.12.4 <u>Verification of state of EEPLDs</u>. When specified, devices shall be verified as either written to the specified pattern or cleared. As a minimum, verification shall consist of performing a read of the entire array to verify that all bits are in the proper state. Any bit that does not verify to be in the proper state shall constitute a device failure and the device shall be removed from the lot or sample.
- 3.13 Endurance. A reprogrammability test shall be completed as part of the vendor's reliability monitor. This reprogrammability test shall be done only for initial characterization and after any design or process changes which may affect the reprogrammability of the device. The methods and procedures may be vendor specific, but will guarantee the number of program/erase endurance cycles listed in section 1.3 herein. The vendors procedure shall be under document control and shall be made available upon request. Endurance capability shall be guaranteed at 25°C only.
- 3.14 <u>Data retention</u>. A data retention stress test shall be completed as part of the vendor's reliability process. This test shall be done initially and after any design or process change which may affect data retention. The methods and procedures may be vendor specific, but will guarantee the number of years listed in section 1.3 herein. The vendors procedure shall be under document control and shall be made available upon request. Data retention capability shall be guaranteed over the full military temperature range.

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4. QUALITY ASSURANCE PROVISIONS

- 4.1 <u>Sampling and inspection</u>. For device class M, sampling and inspection procedures shall be in accordance with MIL-STD-883 (see 3.1 herein). For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-I-38535 and the device manufacturer's QM plan.
- 4.2 <u>Screening</u>. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. For device classes Q and V, screening shall be in accordance with MIL-I-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection.
- 4.2.1 Additional criteria for device class M.
 - a. Delete the sequence specified as initial (preburn-in) electrical parameters through interim (postburn-in) electrical parameters of method 5004 and substitute lines 1 through 6 of table IIA herein.
 - b. Prior to burn-in, the devices shall be programmed (see 4.6 herein) with a checkboard pattern or equivalent (manufacturers at their option may employ an equivalent pattern provided it is a topologically true alternating bit pattern). The pattern shall be read before and after burn-in. Devices having bits not in the proper state after burn-in shall constitute a device failure and shall be included in the Percent Defective Allowable (PDA) calculation and shall be removed from the lot. The manufacturer as an option may use built-in test circuitry by testing the entire lot to verify programmability and AC performance without programming the user array.
 - c. For device class M, the test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. For device class M the test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - (1) Dynamic burn-in for device class M (method 1015 of MIL-STD-883, test condition D); for circuit see 4.2.1c herein.
 - d. Interim and final electrical parameters shall be as specified in table IIA herein.
- 4.2.2 Additional criteria for device classes Q and V.
 - a. The burn-in test duration, test condition, and test temperature or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-I-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
 - b. Interim and final electrical test parameters shall be as specified in table IIA herein.
 - c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-I-38535.
 - d. After the completion of all screening, the devices shall be erased and verified prior to delivery.
- 4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-I-38535. Inspections to be performed shall be those specified in MIL-I-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5).
- 4.4 <u>Conformance inspection</u>. Quality conformance inspection for device class M shall be in accordance with MIL-STD-883 (see 3.1 herein) and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.5). Technology conformance inspection for classes Q and V shall be in accordance with MIL-I-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-I-38535 permits alternate in-line control testing.

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TABLE I. <u>Electrical performance characteristics</u>. Device Limits Unit Test Conditions Group A Symbol 4.5 $V \le V_{CC} \le 5.5 V$ -55°C $\le T_C \le +125$ °C unless otherwise specified subgroups type Min Max $V_{CC} = 4.5 \text{ V}, \quad V_{IH} = 2.0 \text{ V}, \\ I_{OH} = -4.0 \text{ mA}, \quad V_{IL} = -0.8 \text{ V}$ ALL 2.4 1,2,3 Output high voltage VOH 0.45 ٧ $V_{CC} = 4.5 \text{ V}, V_{IH} = 2.0 \text{ V}$ $I_{OL} = 8.0 \text{ mA}, V_{IL} = 0.8 \text{ V}$ 1,2,3 ALL Output low voltage VOL 2.0 ٧ ALL ν_{CC} +0.3 1,2,3 Input high voltage VIH ALL -0.3 0.8 ٧ $^{\rm V}$ IL 1,2,3 Input low voltage $\mathbf{V}_{CC} = 5.5 \text{ V}$ $\mathbf{V}_{IN} = 5.5 \text{ V} \text{ and GND}$ μА ALL -10 10 1,2,3 Input leakage current IIX $v_{\text{CC}} = 5.5 \text{ V}$ $v_{\text{OUT}} = 5.5 \text{ V} \text{ and GND}$ 40 1,2,3 All -40 μA Output leakage Ioz current -100 -225 mА 1,2,3 ALL $^{\rm I}$ sc $v_{OUT} = 0.5 \text{ V}, v_{CC} = 5.5 \text{ V}$ Output short circuit 1/ 2/ current 400 $V_{IN} = V_{CC}$ to GND, $V_{CC} = 5.5$ V, $I_{OUT} = 0$ mA f = 1 MHZ ALL mΑ 1,2,3 Power supply current ¹cc1 (active, low power mode) 3/ 4/ V_{CC} = 5.5 V, I_{CUT} = 9 mA V_{IN} = 6ND 300 mΑ ALL Power supply current I_{CC2} 1,2,3 (standby, low power mode) 3/4/ $v_{CC} = 5.0 \text{ V}, \ v_{IN} = 0.0 \text{ V}, \\ \tau_{A} = +25^{\circ}\text{C}, \quad f = 1 \text{ MHz}$ All c_{IN} Input capacitance 20 рF 0E1n See 4.4.1f 15 All other inputs $v_{CC} = 5.0 \text{ V}, v_{OUT} = 0.0 \text{ V}$ $T_A = +25^{\circ}\text{C}, f = 1 \text{ MHz}$ рF 15 Output capacitance ALL c_{OUT} See 4.4.1f See footnotes at end of table. 5962-93247 SIZE STANDARD

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TABLE I. Electrical performance characteristics - Continued.

Test	Symbol Conditions		Group A subgroups	Device type	LIT	nits	Unit
		4.5 V ≤ V _{CC} ≤ 5.5 V -55°C ≤ T _C ≤ +125°C unless otherwise specified	subgroups	 	Min	Max	
unctional tests		See 4.4.1c	7,8A,8B	ALL			
EXTERNAL TIMING			•	1		1	
Input to nonregistered output	^t PD1	See figures 4 circuit A and 5 <u>5</u> /	9,10,11	01		20	ns
			<u> </u>	02	<u> </u>	15_	
I/O input to non- registered output	t _{PD2}		9,10,11	01		20	ns
		_		02	<u> </u>	15	
Global clock setup	^t fSU		9,10,11	01	5	! ! !	ns
_	_	_		02	3	<u> </u>	<u> </u>
Global clock setup time for fast input 2/	t _{FH}		 9,10,11 	01	2	 	ns
· -			 	02	1	<u> </u>	<u> </u>
Global clock setup time	t _{SU}		9,10,11	01	12	 	ns
			 	02	11	<u> </u>	ļ
Global clock hold time	t _H		9,10,11	ALL	0		ns
Global clock to output	t _{co1}	_	9,10,11	01		12	ns
delay			Ì	02		9.0	
Global clock high time	t _{CH}		9,10,11	01	6.0	i	ns
<u>2</u> / <u>4</u> /	1			02	5.0		<u> </u>
Array clock to output	t _{ACO1}		9,10,11	01		20	ns
delay				02		1 15	

See footnotes at end of table.

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TABLE I. <u>Electrical performance characteristics</u> - Continued.

Test	Symbol	Conditions	Group A subgroups	Device type	Lia	iits	Unit
		4.5 V ≤ V _{CC} ≤ 5.5 V -55°C ≤ T _C ≤ +125°C unless otherwise specified	adogroups 	сурс	Min	Max	
Array clock high time	^t ACH	See figures 4 circuit A and 5 5/	9,10,11	01	8.0		ns
			<u> </u>	02	6.0		
Global clock low time	^t CL		9,10,11	01	6.0		ns
		_{	<u> </u>	02	5.0		
Array clock setup time	^t asu		9,10,11	01	6.0		ns
<u> </u>		_ _	 	02	5.0		
Array clock hold time	t _{AH}	 	 9,10,11 	01	6.0		ns
			 	 02	5.0		<u> </u>
Array clock low time 2/4/	^t ACL		9,10,11	01	 8.0 	 	 ns
<u> </u>				02	6.0_		[<u></u>
Minimum global clock period <u>2</u> / <u>3</u> / <u>4</u> /	^t CNT	_	9,10,11	 01 	 	16	ns
				02_	<u> </u> 	13	<u> </u>
Maximum internal global clock frequency	f _{CNT}	_	9,10,11	01	62.5	 	 MHz
2/3/4/				02	76.9	<u> </u> 	
Minimum array clock period 2/3/4/	^t ACNT		9,10,11	01		16	l ns
per red <u>e</u> , <u>e</u> , <u>r</u> ,				02	l L	13	
Maximum internal array clock frequency	f _{ACNT}	_	9,10,11	01	62.5		 MHz
<u>2</u> / <u>3</u> / <u>4</u> /			 	 02	76.9		<u> </u>
Maximum clock frequency 2/4/6/	f _{MAX}		9,10,11	01	83.3		MHZ
=		İ		02	100		1

See footnotes at end of table.

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Test	Symbol		ditions ≤55 V	Group A subgroups	Device type	Li	nits	Unit
		4.5 V ≤ V _{CC} -55°C ≤ T _C : unless other	≤ +125°C wise specified	i i i i i i i i i i i i i i i i i i i		Min	Max	
INTERNAL TIMING						·		
Input pad and buffer delay	t _{IN}	See figures and 5 5/ 7/		9,10,11	ALL	[3.0	ns
I/O input pad and buffer delay	t _{IO}	- <u> </u> 		9,10,11	ALL		3.0	ns
	^t SEXP	_		9,10,11	01		9.0	ns
		_			02		8.0	
Parallel expander delay	^t PEXP		9,10,11	ALL		2.0	ns	
Logic array delay	^t LAD		9,10,11	01		8.0	ns	
				<u> </u>	02	<u> </u>	5.0	
Logic control array delay	t _{LAC}			9,10,11	01		8.0	ns
		_		 	02		5.0	
Output buffer and pad delay	t _{OD}			9,10,11	01		5.0	ns
		_[<u> </u>	02	<u> </u>	4.0	
Output buffer enable delay	^t zx			9,10,11	01		10	ns
					02	<u> </u>	7	
Output buffer disable delay	^t xz	See figures and 5 5/7	4 circuit B /	9,10,11	01		10	ns
		<u> </u>		<u> </u>	02	<u> </u>	7	
Register setup time	t _{su}	See figures and 5 <u>5</u> / <u>7</u>	4 circuit A	9,10,11	01	4.0		ns
		-			02	5.0		
Global control delay	^t GLOB			9,10,11	01	1	3.0	ns
ee footnotes at end of table		1			02	<u>i</u>	1.0	
STAND MICROCIRCUI	T DRAWING		SIZE A				5962	2-932
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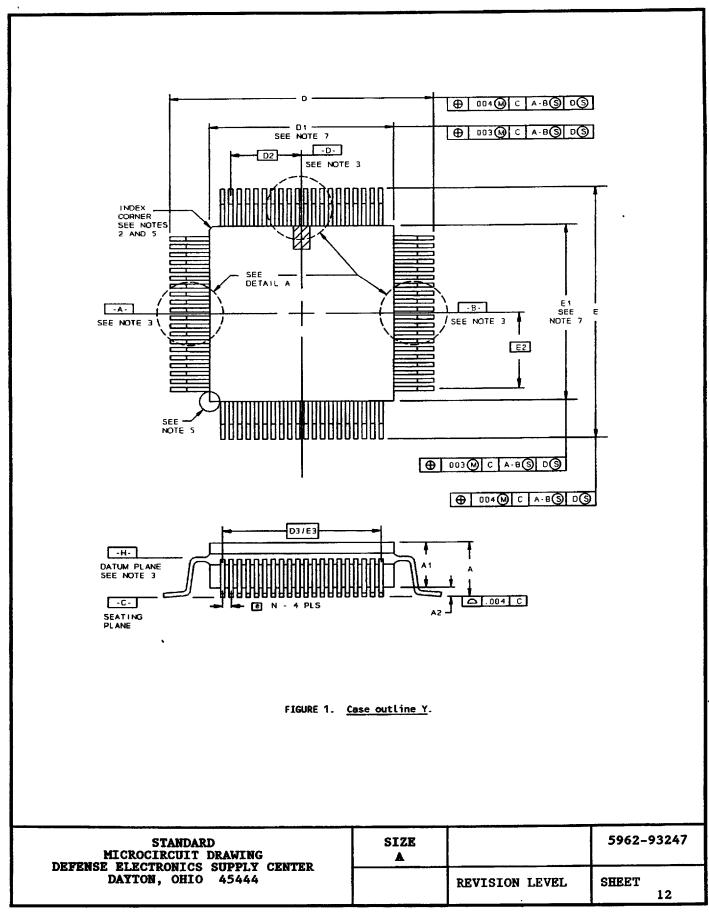
TABLE I. <u>Electrical performance characteristics</u> - Continued.

Test	Symbol	Conditions	Group A	Device type	Lit	nits	Unit
	! 	4.5 $V \le V_{CC} \le 5.5 V$ -55°C $\le T_C \le +125$ °C unless otherwise specified	anna onha		Min	Max	
Register hold time	t _H	See figures 4 circuit A and 5 5/7/	9,10,11	ALL	5.0		ns
Register delay	† _{RD}		9,10,11	ALL		1.0	ns
Combinatorial delay	tcomb	 	9,10,11	ALL		1.0	ns
Array clock delay	t _{IC}	_ <u> </u>	9,10,11	01		8.0	ns
				02	<u> </u>	5.0	
Register enable time	t _{EN}		9,10,11	01		8.0	 ns
			 	02	<u> </u>	5.0	<u> </u>
Register preset time	t _{PRE}	_ 	9,10,11	ALL		4.0	 ns
Register clear time	tcLR		9,10,11	ALL		4.0	ns
Program interconnect array delay	t _{PIA}	_	9,10,11	01		3.0	ns
				02	ļ	2.0	<u> </u>
Low power adder	t _{LPA}		9,10,11	01		15	l ns
			<u> </u>	02		13	<u> </u>
Slew rate adder 9/	^t SRA	1	9,10,11	ALL		4	ns

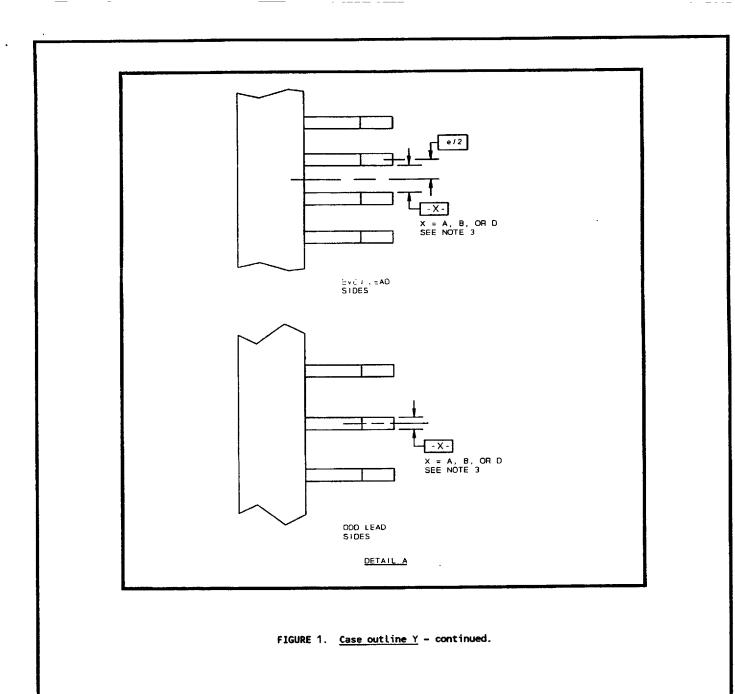
- 1/ Not more than one output at a time should be shorted. Short circuit test duration should not exceed 1.0 second.
- $\frac{2}{2}$ / Tested initially and after any design or process changes that affect the parameter, and therefore shall be guranteed to the limits specified in table ${\bf I}.$
- 3/ Specified with a device programmed as a 16-bit loadable, enabled, up/down counter in each LAB.
- 4/ Values are guaranteed by design and may not be tested directly.
- 5/ AC tests are specified with input rise and fall times (10 percent to 90 percent) at 3.0 ns, timing reference levels of 1.5 V, input pulse levels of 0 V to 3.0 V, and the output load of figure 3, circuit A.
- 6/ f_{MAX} represents the highest frequency for pipelined data.
 7/ Internal timing parameters are not directly measurable and therefore are guaranteed by testing external timing parameters.
- The t_{LPA} parameter must be added to the t_{LAD} , t_{LAC} , t_{ACL} , t_{EN} , and t_{SEXP} parameters for macrocells running in low power mode.
- 9/ The t_{SRA} parameter must be added to the t_{OD} and t_{IX} parameters for outputs set to slow slew rate.

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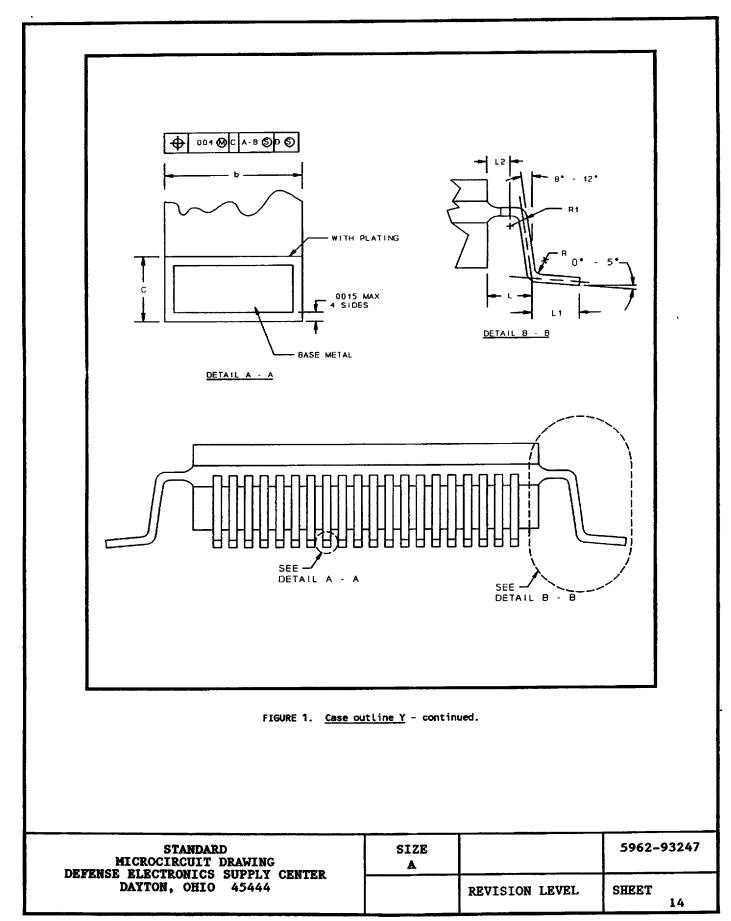


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STANDARD MICROCIRCUIT DRAWING	SIZE		5962-93247
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0		208 pin CQFP	Notes
Symbol	Man	Max	Notes
A	2.16	4.83	1,2
A1	1.91	3.81	1
A2	0.20	1.02	1
b	0.20	0.56	1
c	0.19	0.28	ĺ
D/E	30.4	30.8	
D1/E1	26.9	27.5	2,3
D2/E2		12.75 BSC	,
D3/E3		25.5 BSC	!
e		0.50 BSC	1
Ľ		1.20 REF	ţ
Lī	0.30		1
L2		0.82 REF	l
R	0.20		
R1		N/A	1
ND/NE		52	4
N		208	į 4,5

- 1. Controlling dimensions are in milimeters.
- 2. Dimension "A" controls the overall package height. When a window lid is used, dimension "A" must increase by a minimum of .010 inch (0.254 mm) and a maximum of .040 inch (1.020 mm).
- 3. Chip carriers shall be constructed of a minimum of two ceramic layers.
- This dimension allows for package edge anomalies caused by material protrusion, such as rough ceramic, misaligned ceramic layers and lids, meniscus, and glass overrun.
- 5. Symbol "N" is the maximum number of terminals. Symbols "ND" and "NE" are the number of terminals along the sides of lengths "D" and "E" respectively.
- 6. A terminal 1 identification mark shall be located on the first side clockwise from the index corner, within the shaded area shown. Terminal numbers shall increase in a counterclockwise direction when viewed as shown. If the identification mark is not exactly adjacent to terminal 1, terminal 1 is located as follows:
 - a. If the number of terminals on a side is odd, terminal 1 is the center terminal.
 - b. If the number of terminals on a side is even, terminal 1 is the terminal which is adjacent to the centerline of the terminal array in the direction closest to the index corner.
- 7. When the number of terminals per side is even, datums A, B, and D are located at the terminal array centers. When the number of terminals per side is odd, datums A, B, and D are located at the centers of the center terminals. The measurement point for establishing these datums is the package/lead interface at datum plane H.
- 8. Corner shape (square, notch, radius, etc.) may vary from that shown on the drawing. The index corner shall be clearly unique.
- 9. The leads on this package style shall be protected from mechanical distortion and damage such that dimensions pertaining to relative lead/body "true positions" and lead "coplanarity" are always maintained until the next higher level package attachment process is complete. Package lead protection mechanisms (tie bars, carriers, etc.) are not shown on the drawing; however, when microcircuit devices contained in this package style are shipped for use in Government equipment, or shipped directly to the Government as spare parts or mechanical qualification samples, lead protection shall be in place.
- 10. The quad leaded chip carrier drawings in this figure show a "gullwing" lead configuration. An optional lead configuration can be specified for unformed (straight) leads, see figure 1 and table V concerning how to designate an option. When either option is selected and straight leads are subsequently formed by the microcircuit device user, the resultant lead configuration shall conform to the "gullwing" lead dimensions and coplanarity requirements specified in this figure.

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Case outline X ALL All Device Device Device ALL type type type Terminal Terminal Terminal Terminal Terminal Terminal symbol number symbol number symbol number E16 C1/0 01/0 **C1 A1** P1/0 CI/O E17 с2 01/0 **A2** P1/0 01/0 F1 KI/O С3 A3 PI/O F2 01/0 A4 PI/O C4 PI/O KI/O A5 C5 VCC F3 LI/O F15 GI/O LI/O **c6 A6** LI/O F16 CI/O A7 LI/O **C7** GND GI/O LI/O F17 С8 **A8** LI/O G1 KI/O HI/O С9 **A9** LI/O KI/O A10 HI/O €10 HI/O G2 G3 KI/O C11 VCC A11 HI/O G4 VCC A12 H1/0 c12 HI/O G14 GND GND HI/O C13 A13 G15 G1/0 DI/O **C14** A14 D1/0 GI/O G16 A15 DI/O c15 C1/0 G17 GI/O 0/13 **C16** A16 DI/O KI/O н1 A17 01/0 **C17** CI/O D1 01/0 H2 KI/O В1 01/0 н3 KI/O 82 PI/O D2 01/0 GND H4 03 01/0 83 PI/O H14 VCC **GNDO** D4 **B**4 P1/0 H15 GI/O **B**5 PI/O **D7** VCC GND H16 GI/0 80 **B6** PI/O GI/O H17 LI/O **D9** HI/O в7 KI/O D10 GND J1 88 LI/O J2 JI/O В9 L1/0 D11 ACC J3 J1/0 B10 D14 VCC HI/O **J**4 JI/O C1/0 **B11** HI/O D15 J14 FI/0 D16 CI/O 812 D1/0 CI/O J15 FI/O D17 B13 DI/O J16 FI/O 01/0 E1 01/0 **B14** KI/0 j17 GI/O E2 B15 DI/O **B16** DI/O E3 01/0 E15 CI/O DI/O **B17**

NC = NO CONNECT

FIGURE 2. Terminal connections.

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Case outline X Device ALL ALL Device ALL Device type type type Terminal Terminal Terminal Terminal Terminal Terminal symbol symbol number symbol number number 11/0 **U8** NI/O K1 JI/O R1 R2 MI/O U9 11/0 JI/O K2 U10 E1/0 MI/O кЗ JI/0 R3 E1/0 VCC R4 GND **U11** Κ4 R5 VCC U12 E1/0 K14 GND AI/O **U13** 11/0 K15 FI/0 R6 AI/O FI/O R7 11/0 U14 K16 11/0 U15 AI/O **R8** K17 **FI/O** AI/O **U16** L1 JI/O R9 **GCLRK** JI/O R10 EI/O U17 AI/O 12 GND R11 L3 JI/O L4 GND R12 EI/O R13 EI/O L14 VCC R14 VCC L15 FI/O L16 FI/O R15 AI/O AI/O L17 FI/O R16 M1 JI/O R17 BI/O T1 NI/O M2 NI/O NI/O M3 NI/O T2 M15 B1/0 T3 MI/0 T4 M1/0 M16 BI/O M17 FI/O T5 MI/O 11/0 **T6** N7 NI/O N2 NI/O **T7** 11/0 Т8 11/0 NI/O Ν3 τ9 11/0 N15 BI/O N16 BI/0 T10 EI/O EI/O N17 T11 BI/O Р1 NI/O T12 EI/O

NC = NO CONNECT

NI/O

VCC

MI/O

VCC

GCCKI

GND

VCC

AI/O

GND

BI/O

BI/O

P2

Р3

P4

₽7

P8 P9

P10

P11

P14

P15

P16

P17

FIGURE 2. <u>Terminal connections</u> - Continued.

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- 9004708 0012928 501 **-**

T13

T14

T15

T16

T17

U1

U2

U3

U4 U5

U6

U7

EI/O

AI/O

AI/O

BI/O

BI/O

MI/O

MI/O

MI/O

MI/0

11/0

11/0

Case outline Y Device Device Device Device ALL ALL type type ALL type ALL type Terminal Terminal Terminal Terminal Terminal Terminal Terminal Terminal number symbol symbol symbol symbol number number number 157 NC NÇ 105 NC NC 53 NC 158 NC NC 54 NC 106 2 AI/O 55 PI/O 107 VCCio 159 MI/O 3 160 AI/O CI/O 108 4 56 P1/0 MI/O AI/O 161 5 57 PI/O 109 CI/O VCCio 110 CI/O 162 AI/O 58 P1/0 6 NI/O AI/O 163 CI/O 7 NI/O 59 P1/0 111 164 AI/O 60 PI/0 112 CI/O 8 NI/O 165 **VCCio** 113 CI/O 61 PI/O 9 NI/O AI/O 166 CI/O 10 NI/O 62 0/19 114 167 VCCio 115 CI/O AI/O 63 11 NI/O 168 EI/O GND 116 12 NI/O 64 PI/O 169 EI/O 13 65 PI/O 117 C1/0 NI/O CI/O 170 EI/O LI/O 118 66 14 GND EI/O 171 GI/O 15 NI/O 67 LI/O 119 EI/O 172 68 LI/O 120 GI/0 16 NI/O 173 EI/O GI/O 121 17 JI/O 69 LI/O GND 174 70 LI/O 122 GI/O 18 JI/0 123 **GI/O** 175 EI/O 71 19 J1/0 LI/O EI/O 176 GI/0 20 JI/O 72 GND 124 125 **VCCio** 177 EI/O 73 LI/O 21 JI/O 178 EI/O G1/0 JI/0 74 **VCC1nt** 126 22 **VCCint** 179 75 GND 127 GI/O 23 **VCCio** GI/O 180 GND 128 24 JI/O 76 LI/O OE2/GCLK2 LI/O 129 GI/O 181 25 JI/O 77 130 F1/0 182 GCLRn 26 J1/0 78 LI/O 183 0E1 79 HI/O 131 F1/0 27 J1/0 80 HI/O 132 FI/O 184 GCLK1 28 KI/O 185 GND 29 81 HI/O 133 FI/O KI/O **VCCint** 134 GND 186 82 GND 30 KI/O FI/0 187 11/0 135 31 K1/0 83 **VCCint** 11/0 188 HI/O 136 FI/0 32 84 GND 189 11/0 137 F1/0 33 KI/O 85 **VCCio** 190 11/0 34 86 HI/O 138 F1/0 KI/D FI/O 191 VCCio 87 HI/O 139 35 KI/O 192 11/0 36 88 HI/O 140 FI/O KI/O 141 BI/O 193 11/0 37 89 HI/O K1/0 11/0 BI/0 194 142 38 KI/O 90 HI/O 195 11/0 91 143 **VCCio** 39 HI/O 01/0 196 11/0 144 BI/0 40 01/0 92 DI/O 197 11/0 93 DI/O 145 BI/O 41 VCC10 94 146 BI/O 198 MI/O GND 42 01/0 199 MI/O 95 01/0 147 B1/0 43 01/0 148 B1/0 200 GND 96 DI/O 44 01/0 MI/O 97 149 RI/O 201 45 01/0 DI/O 202 MI/O 98 01/0 150 BI/O 01/0 46 203 0/1M 151 **BI/O** 47 99 DI/O 01/0 204 MI/O 48 100 D1/0 152 GND 01/0 MI/O AI/O 205 101 DI/O 153 49 01/0 206 MI/O 154 AI/O 50 **GND** 102 DI/O NC 155 NC 207 51 NC 103 NC 208 NC 156 NC 104 NC 52 NC

NC = NO CONNECT

FIGURE 2. Terminal connections - Continued.

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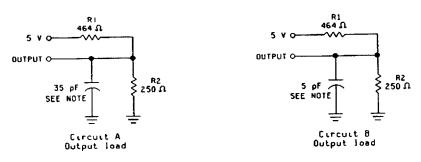
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		Truth table		
		Input pins		Output pins
LRn/I	0E2n/I	CLK/I	I	1/0
CLKn/1	OEZII/ I		V	7

NOTES:

- X = Don't care.
 Z = High impedance.

FIGURE 3. Truth table (unprogrammed).



NOTE: Including scope and jig (minimum values).

AC test conditions

Input pulse levels	GND to 3.0 V
Input rise and fall levels	≤ 3 ns
Input timing reference levels	1.5 V
Output reference levels	1.5 V

Input pulses

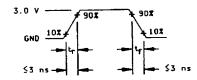


FIGURE 4. Output load circuits and test conditions.

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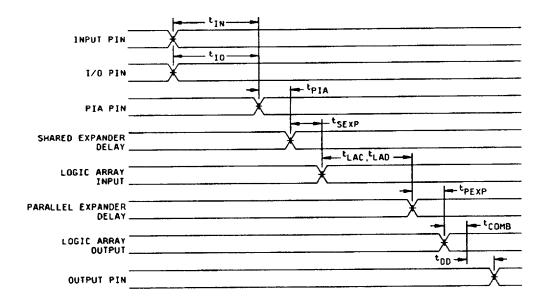
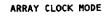


FIGURE 5. Switching waveforms.

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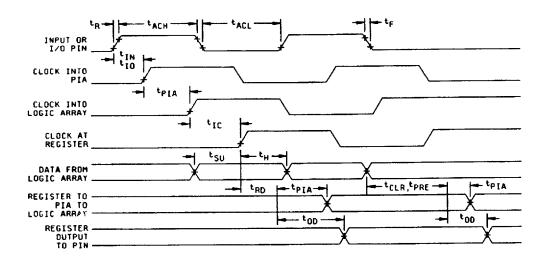


FIGURE 5. Switching waveforms - Continued.

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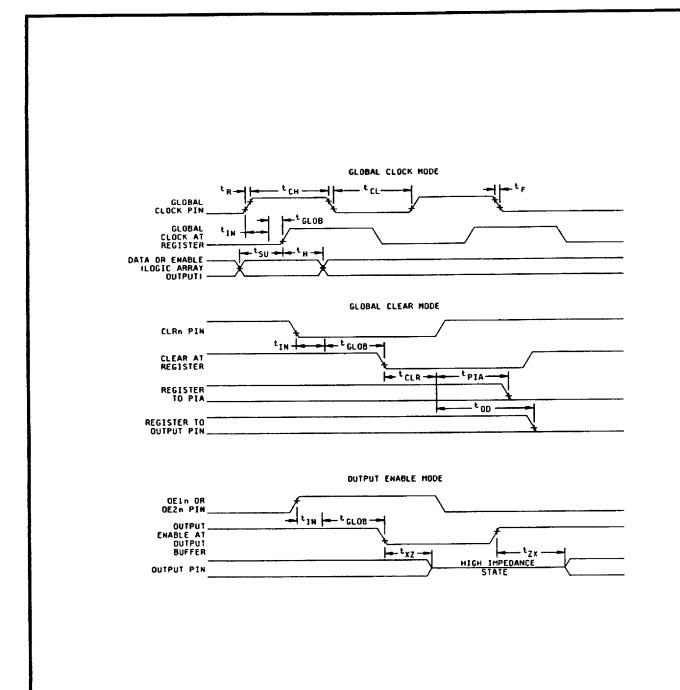


FIGURE 5. Switching waveforms - Continued.

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4.4.1 Group A inspection.

- a. Tests shall be as specified in table IIA herein.
- b. Subgroups 5 and 6 of Table I of method 5005 of MIL-STD-883 shall be omitted.
- c. For device class M subgroups 7 and 8 tests shall be sufficient to verify the truth table. For device classes Q and V subgroups 7 and 8 shall include verifying the functionality of the device; these tests shall have been fault graded in accordance with MIL-STD-883, test method 5012 (see 1.5 herein).
- d. All devices selected for testing shall be programmed with a checkerboard pattern or equivalent. After completion of all testing, the devices shall be erased and verified, (except devices submitted for groups B, C, and D testing).
- e. O/V (latch-up) tests shall be measured only for initial qualification and after any design or process changes which may affect the performance of the device. For device class M procedures and circuits shall be maintained under document revision level control by the manufacturer and shall be made available to the preparing activity or acquiring activity upon request. For device classes Q and V, the procedures and circuits shall be under the control of the device manufacturer's (TRB) in accordance with MIL-I-38535 and shall be made available to the preparing activity or acquiring activity upon request. Testing shall be on all pins, on 5 devices with zero failures. Latch-up test shall be considered destructive. Information contained in JEDEC standard number 17 may be used for reference.
- f. Subgroup 4 (C_{IN} and C_{OUT} measurements) shall be measured only for initial qualification and after any process or design changes which may affect input or output capacitance. Capacitance shall be measured between the designated terminal and GND at a frequency of 1MHz. Sample size is five devices with no failures, and all input and output terminal tested.
- 4.4.2 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shall be as specified in table IIA herein. Delta limits shall apply only to subgroup 1 of group C inspection and shall consist of tests specified in table IIB herein.
 - 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. The devices selected for testing shall be programmed (see 3.2.3.1 herein). After completion of all testing the devices shall be erased and verified (except devices submitted to group D).
 - b. Test condition D. For device class M, the test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
 - b. $T_A = +125$ °C, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.
- 4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-I-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-I-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
- 4.4.3 <u>Group D inspection</u>. For group D inspection end-point electrical parameters shall be as specified in table IIA herein. The devices selected for testing shall be programmed (see 3.2.3.2 herein). After completion of all testing, the devices shall be erased and verified.

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TABLE IIA. <u>Electrical test requirements</u>. <u>1/ 2/ 3/ 4/ 5/ 6/ 7/</u>

Line	Test	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-I-38535, table III)			
no.	requirements	Device class M	Device class Q	Device class V		
1	Interim electrical parameters (see 4.2)			1,7,9		
2	Static burn-in I and II (method 1015)	Not required	Not required	Required		
3	Same as line 1			1*,7* A		
4	Dynamic burn-in (method 1015)	Required	Required	Required		
5	Same as line 1			1*,7* A		
6	Final electrical parameters	 1*,2,3,7*, 8A,8B,9,10, 11	 1*,2,3,7*, 8A,8B,9,10, 11	1*,2,3,7*, 8A,8B,9, 10,11		
7	Group A test requirements	1,2,3,4**,7, 3A,8B,9,10, 11	1,2,3,4**,7, 8A,8B,9,1C, 11	1,2,3,4**,7, 8A,8B,9,10,		
8	Group C end-point electrical parameters	2,3,7, 8A,8B	1,2,3,7, 8A,8B	1,2,3,7, 8A,8B,9, 10,11 Δ		
9	Group D end-point electrical parameters	2,3, 8A,8B	2,3, 8A,8B	2,3, 8A,8B		
10	Group E end-point electrical parameters	1,7,9	1,7,9	1,7,9		

- 1/ Blank spaces indicate tests are not applicable.
- 2/ Any or all subgroups may be combined when using high-speed testers.
- 3/ Subgroups 7 and 8 functional tests shall verify the truth table. 4/ * indicates PDA applies to subgroup 1 and 7. 5/ ** see 4.4.1f.

- $\frac{1}{6}$ / Δ indicates delta limit (see table IIB) shall be required where specified, and the delta values shall be computed with reference to the previous interim electrical parameters (see line 1).
- 7/ See 4.4.1e.

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TABLE IIB. Delta limits at +25°C.

Parameter <u>1</u> /	Device types
	ALL
I _{CC2}	±1% of specified limit in table I.
IIX	±1% of specified limit in table I.

- 1/ The above parameter shall be recorded before and after the required burn-in and life tests to determine the delta.
- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein). RHA levels for device classes Q and V shall be M, D, R, and H and for device class M shall be M and D.
 - a. End-point electrical parameters shall be as specified in table IIA herein.
 - b. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-I-38535, appendix A, for the RHA level being tested. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-1-38535 for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at $T_A = +25\,^{\circ}\text{C}$ ±5°C, after exposure, to the subgroups specified in table IIA herein.
 - c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.
- 4.5 <u>Delta measurements for device class V.</u> Delta measurements, as specified in table IIA, shall be made and recorded before and after the required burn-in screens and steady-state life tests to determine delta compliance. The electrical parameters to be measured, with associated delta limits are listed in table IIB. The device manufacturer may, at his option, either perform delta measurements or within 24 hours after burn-in perform final electrical parameter tests, subgroups 1, 7, and 9.
- 4.6 <u>Programming procedures</u>. The programming procedures shall be as specified by the device manufacturer and shall be made available upon request.
- 4.7 <u>Erasing procedures</u>. The erasing procedures shall be as specified by the device manufacturer and shall be made available upon request.
 - 5. PACKAGING
- 5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-STD-883 (see 3.1 herein) for device class M and MIL-I-38535 for device classes ℚ and V.
- NOTES
 (This section contains information of a general or explanatory nature that may be helpful, but is not mandatory).
- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
 - 6.1.2 Substitutability. Device class Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-93247
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- 6.3 <u>Record of users.</u> Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and which SMD's are applicable to that system. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DESC-EC, telephone (513) 296-6047.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DESC-EC, Dayton, Ohio 45444, or telephone (513) 296-5377.
- 6.5 <u>Abbreviations, symbols, and definitions.</u> The abbreviations, symbols, and definitions used herein are defined in MIL-I-38535, MIL-STD-1331, and as follows:

CTN	C,	417					٠						Input and bidirectional output, terminal-to-GND capacitance
GŃĎ													Input and bidirectional output, terminal-to-GND capacitance Ground zero voltage potential
Icc	-										-		Supply current
1,,													Input current low
IIH							-	-	-				Input current high
ΤĈ.										-			Case temperature
T.							-						Ambient temperature
۷ _C C											-		Positive supply voltage
οŻΫ												-	Latch-up over-voltage

6.5.1 Waveforms.

Waveform symbol	Input	Output
	MUST BE VALID	WILL BE VALID
	CHANGE FROM H TO L	WILL CHANGE FROM H TO L
	CHANGE FROM L TO H	WILL CHANGE FROM L TO H
XXXXXXX	DON'T CARE ANY CHANGE PERMITTED	CHANGING STATE UNKNOWN
		HIGH IMPEDANCE

6.6 One part - one part number system. The one part - one part number system described below has been developed to allow for transitions between identical generic devices covered by the three major microcircuit requirements documents (MIL-H-38534, MIL-I-38535, and 1.2.1 of MIL-STD-883) without the necessity for the generation of unique PIN's. The three military requirements documents represent different class levels, and previously when a device manufacturer upgraded military product from one class level to another, the benefits of the upgraded product were unavailable to the Original Equipment Manufacturer (OEM), that was contractually locked into the original unique PIN. By establishing a one part number system covering all three documents, the OEM can acquire to the highest class level available for a given generic device to meet system needs without modifying the original contract parts selection criteria.

Military documentation format	Example under ne	PIN ew system	Manufacturing source listing	Document <u>listing</u>
New MIL-H-38534 Standard Microcircuit Drawings	5962-XXXXX	ZZ(H or K)YY	OML-38534	MIL-BUL-103
New MIL-I-38535 Standard Microcircuit Drawings	5962-XXXXX	ZZ(Q or V)YY	QML-38535	MIL-BUL-103
New 1.2.1 of MIL-STD-883 Standard Microcircuit Drawings	5962-XXXXX	ZZ(M)YY	MIL-BUL-103	MIL-BUL-103
STANDARD MICROCIRCUIT DRAWIN	-	SIZE	T	5962-93247
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- 6.7.1 <u>Sources of supply for device classes Q and V.</u> Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DESC-EC and have agreed to this drawing.
- 6.7.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-BUL-103. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DESC-EC.

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